N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

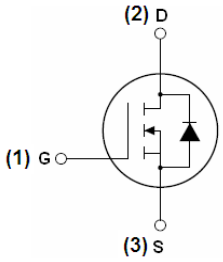
The HM4302 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

GENERAL FEATURES

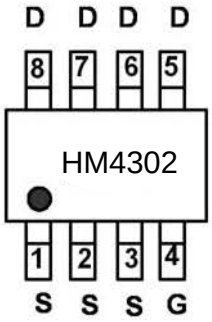
- V_{DS} =30V,I_D =27A
  $R_{DS(ON)}$ < 4.0mΩ @ V_{GS}=10V
  $R_{DS(ON)}$ < 6.0mΩ @ V_{GS}=5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

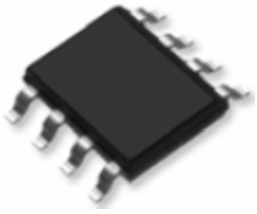
- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



Schematic diagram



Marking and pin Assignment



SOP-8 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM4302	HM4302	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	27	A
Drain Current-Continuous(T_A=100℃)	I_D (100℃)	19	A
Pulsed Drain Current	I_{DM}	80	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient(Note 2)	$R_{\theta JA}$	42	℃/W

Electrical Characteristics (TA=25℃unless otherwise noted)

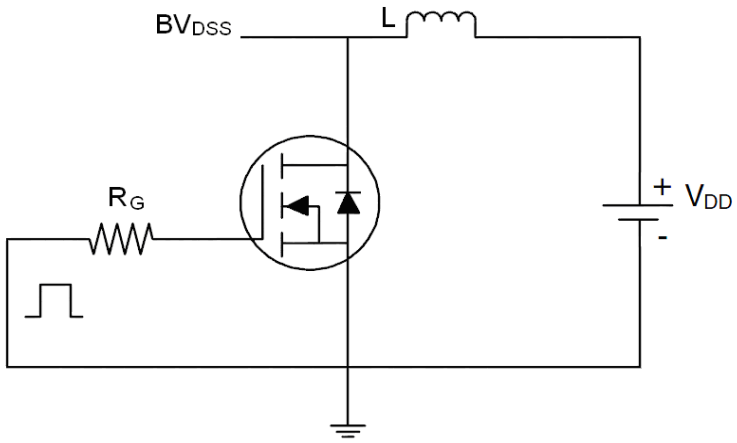
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.2	1.6	2.4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=13A	-	3.0	4.0	mΩ
		V_{GS}=5V, I_D=13A	-	4.3	6.0	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=27A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	2100	-	PF
Output Capacitance	C_{oss}		-	460	-	PF
Reverse Transfer Capacitance	C_{rss}		-	230	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,I_D=13A V_{GS}=10V,R_{GEN}=2.7Ω	-	20	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	60	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=10A, V_{GS}=10V	-	41	-	nC
Gate-Source Charge	Q_{gs}		-	14	-	nC
Gate-Drain Charge	Q_{gd}		-	11	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=13A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	27	A

Notes:

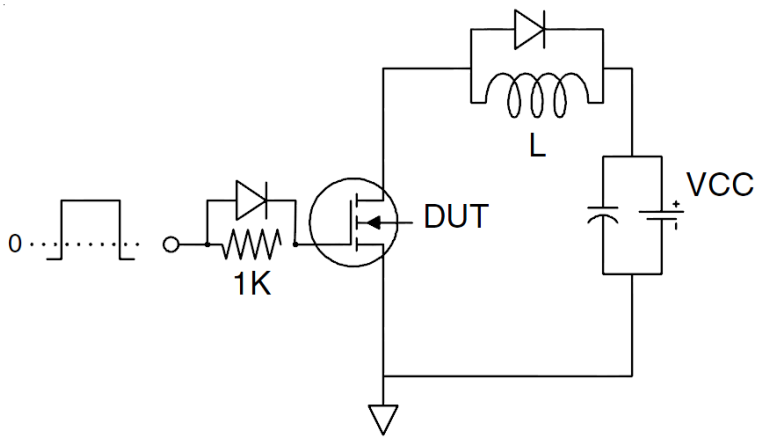
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test circuit

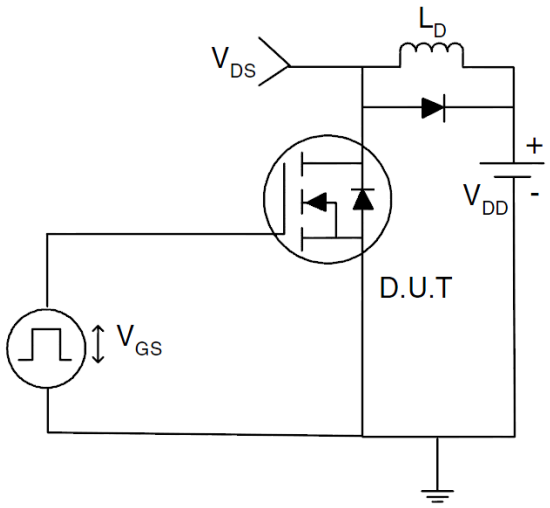
1）E_{AS} test Circuits



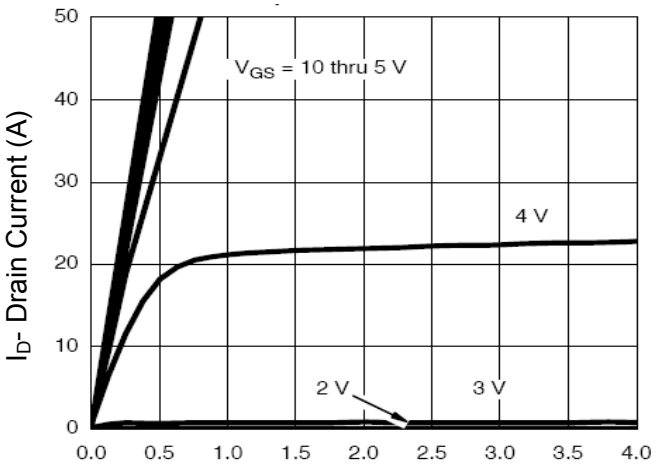
2）Gate charge test Circuit:



3）Switch Time Test Circuit：

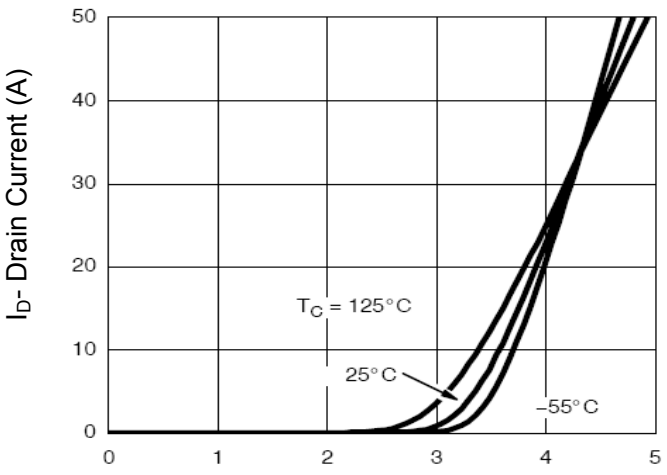


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)



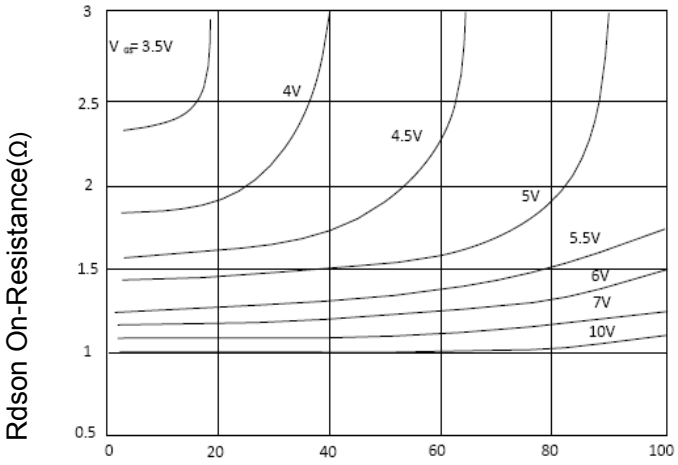
Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



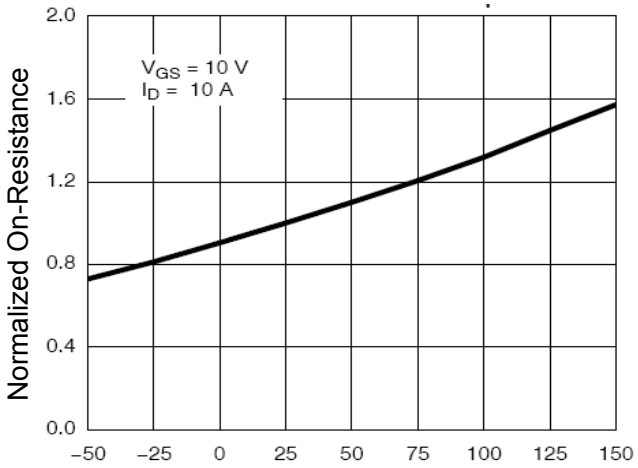
Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics



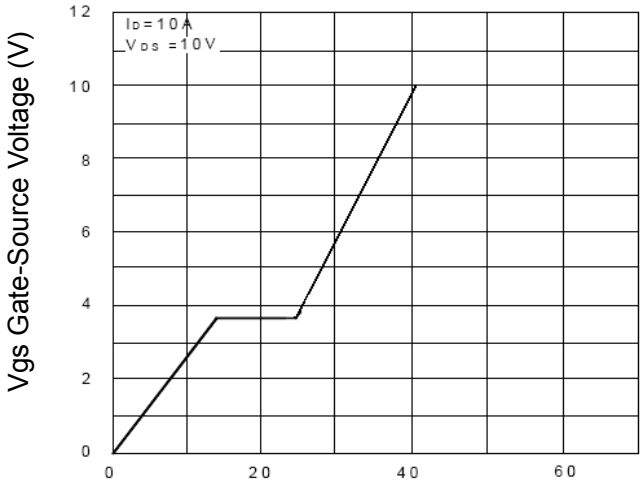
I_D- Drain Current (A)

Figure 3 Rdson- Drain Current



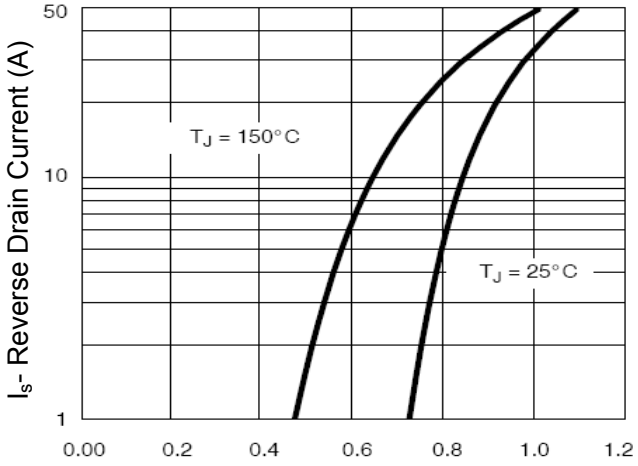
T_J-Junction Temperature(℃)

Figure 4 Rdson-JunctionTemperature



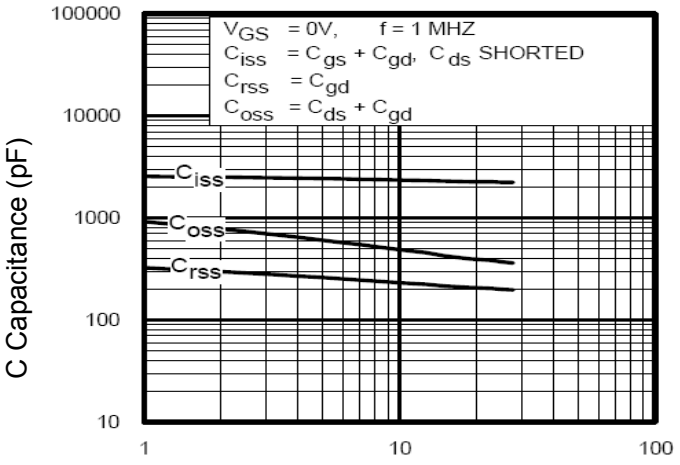
Qg Gate Charge (nC)

Figure 5 Gate Charge



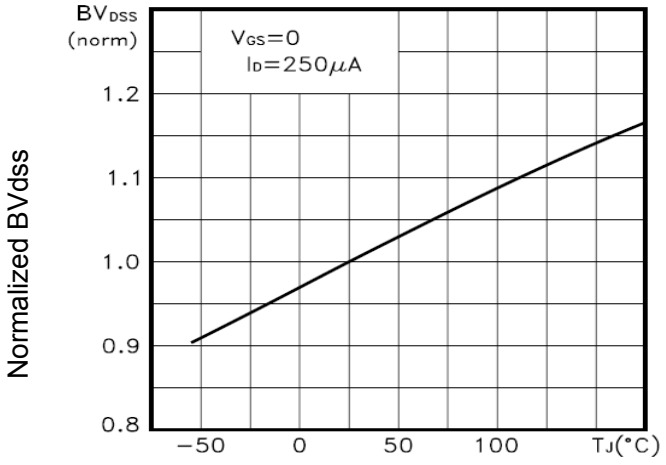
Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



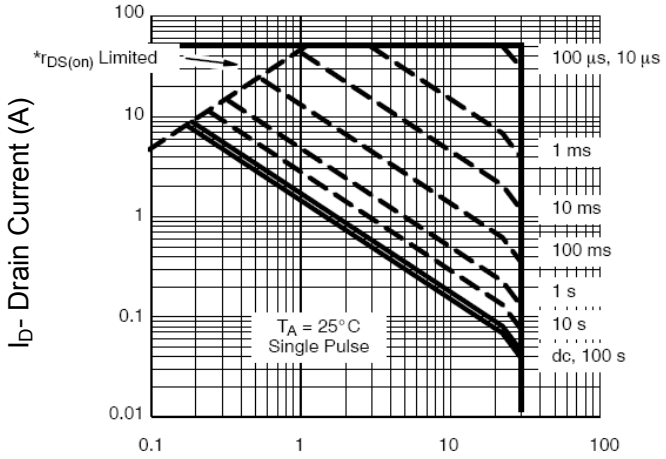
Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



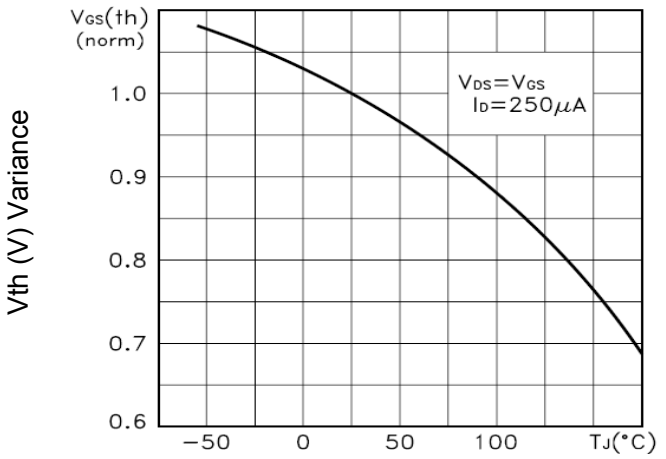
T_J-Junction Temperature(℃)

Figure 9 BV_{DSS} vs Junction Temperature



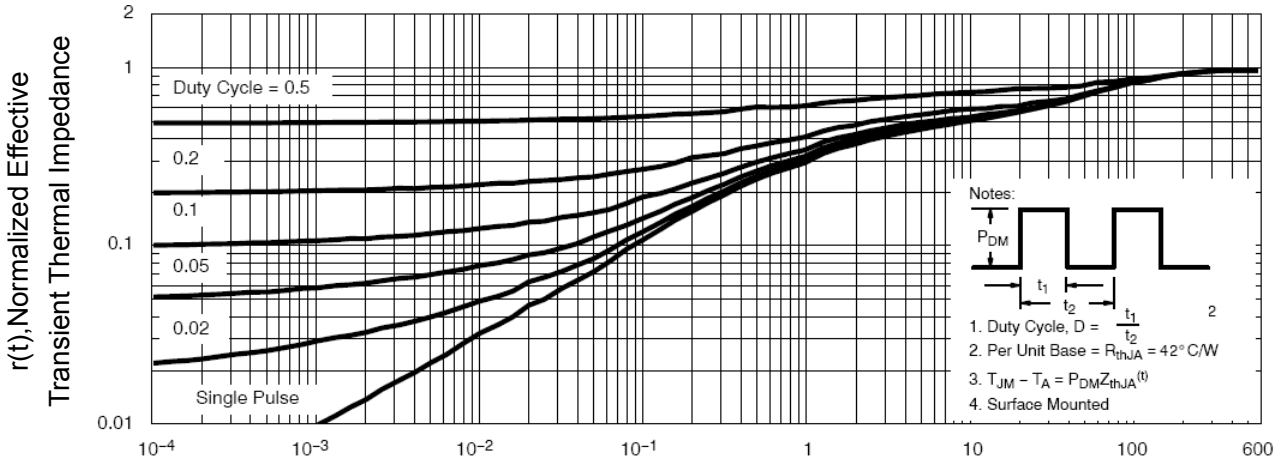
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



T_J-Junction Temperature(℃)

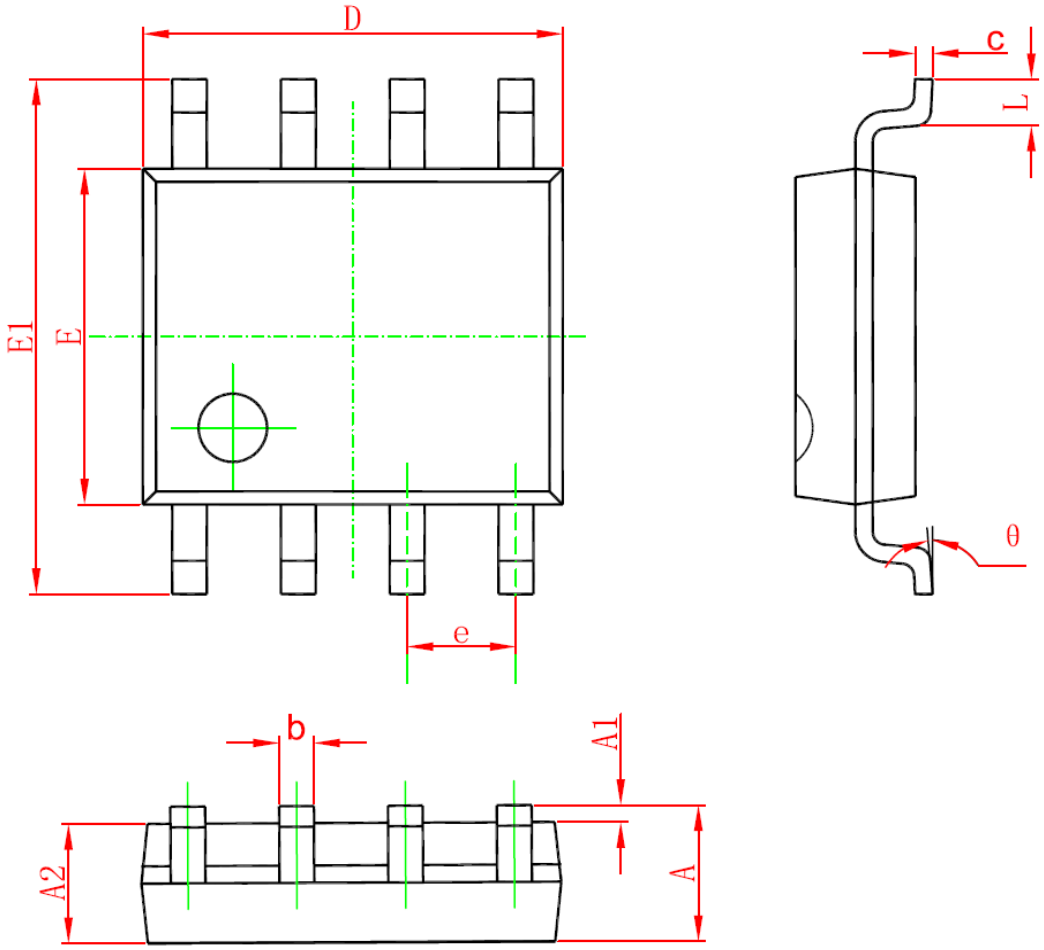
Figure 10 $V_{GS(th)}$ vs Junction Temperature



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 PACKAGE IN FORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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